Power MOSFET

8 V, 4.3 A, High Side Load Switch with Level Shift, 2x2 mm WDFN Package

Features

- WDFN 2x2 mm Package with Exposed Drain Pads Offers Excellent Thermal Performance
- Low R_{DS(on)} P-Channel Load Switch with N-channel MOSFET for Level Shift
- N Channel Operated at 1.5 V Gate Drive Voltage Level
- P Channel Operated at 1.5 V Supply Voltage
- Same Footprint as SC88
- Low Profile (<0.8 mm) Allows it to Fit Easily into Extremely Thin **Environments**
- ESD Protection
- These are Pb-Free Devices

Applications

- High Slide Load Switch with Level Shift
- Optimized for Power Management in Ultra Portable Equipment

MOSFET(Q2) MAXIMUM RATINGS

 $(T_J = 25^{\circ}C \text{ unless otherwise stated})$

Parameter			Symbol	Value	Unit
Q2 Input Voltage (V _{DS} , P-Channel)			V _{IN}	8	V
Q1 On/Off Voltage (\)	Q1 On/Off Voltage (V _{GS} , N-Channel)			6	V
Continuous Load	Steady	Steady T _A = 25°C	Ι _L	4.3	Α
Current (Note 1)	State	T _A = 85°C		3.1	
Power Dissipation (Note 1)	Steady State	T _A = 25°C	P _D	1.56	W
Continuous Load		T _A = 25°C	Ι _L	2.5	Α
Current (Note 2)	Steady	T _A = 85°C		1.8	
Power Dissipation (Note 2)	State	T _A = 25°C	P _D	0.52	W
Pulsed Load Current	t _p = 10 μs		I _{LM}	20	Α
Operating Junction and Storage Temperature			T _J , T _{STG}	–55 to 150	°C
Source Current (Body Diode) (Note 2)			I _S	-2.7	Α
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

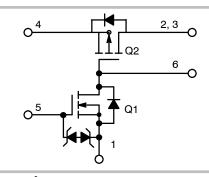
- Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces)
- 2. Surface-mounted on FR4 board using the minimum recommended pad size.



ON Semiconductor®

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V _{INMAX}	R _{DS(on)} MAX	I _L MAX
20 V	50 mΩ @ 4.5 V	
	60 mΩ @ 2.5 V	4.3 A
	80 mΩ @ 1.8 V	4.5 A
	115 mΩ @ 1.5 V	





MARKING DIAGRAM

JN M= 5

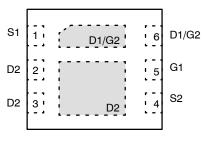
= Specific Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

PIN CONNECTIONS



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 3)	$R_{ heta JA}$	80	°C/W
Junction-to-Ambient - t ≤ 5 s (Note 3)	$R_{ heta JA}$	38	°C/W
Junction-to-Ambient - Steady State Min Pad (Note 4)	$R_{ heta JA}$	180	°C/W

Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
 Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS							
Q2 Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V_{GS} = 0 V, I_D = 250 μA		-8.0			V
Q2 Forward Leakage Current	I _{FL}	V _{ON/OFF} = 0 V,	$V_{ON/OFF} = 0 \text{ V},$ $T_{J} = 25^{\circ}\text{C}$			0.1	μΑ
		V _{IN} = 8.0 V	T _J = 85°C			1	
Q1 Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS1} = ±6 V				±100	nA
Q1 Diode Forward On-Voltage	V_{SD}	$I_S = -1.0 \text{ A}, V_{GS1} = 0 \text{ V}$			-0.8	-1.1	V
ON CHARACTERISTICS	•					•	
Q1 ON/OFF Voltage	V _{ON/OFF}			1.5		8.0	
Q1 Gate Threshold Voltage	V _{GS1(TH)}	V _{GS1} = V _{DS1} , I _D = 250 μA		0.40		1.0	V
Q2 Input Voltage	V _{IN}			1.8		8.0	V
Q2 Drain-to-Source On	R _{DS(on)}	$V_{IN} = 4.5 \text{ V}, I_L = 4.0 \text{ A}$ $V_{IN} = 2.5 \text{ V}, I_L = 3.0 \text{ A}$			33	50	mΩ
Resistance					40	60	1
		V _{IN} = 1.8 V, I _L = 1.7 A			60	80	
		V _{IN} = 1.5 V, I _L :	= 1.2 A		75	115	
Q2 Load Current	Ι <u>L</u>	$V_{DROP} \le 0.2 \text{ V}, V_{IN} = 2.5 \text{ V}, V_{ON/OFF} = 1.5 \text{ V}$		1.0			Α
		$V_{DROP} \le 0.3 \text{ V}, V_{IN} = 1.8 \text{ V}, V_{ON/OFF} = 1.5 \text{ V}$		1.0			

TYPICAL PERFORMANCE CURVES ($T_J = 25^{\circ}C$ unless otherwise noted)

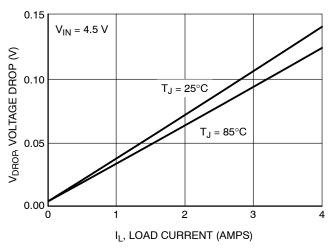


Figure 1. Voltage Drop versus Load Current @ $V_{IN} = 4.5 \text{ V}$

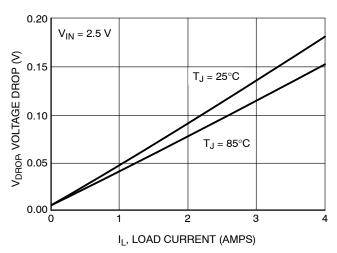


Figure 2. Voltage Drop versus Load Current @ V_{IN} = 2.5 V

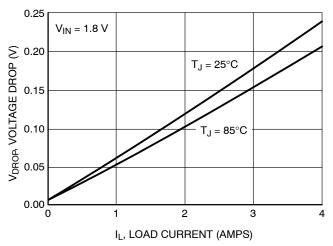


Figure 3. Voltage Drop versus Load Current @ $V_{\text{IN}} = 1.8 \text{ V}$

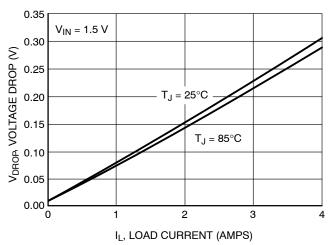
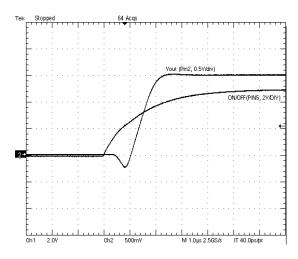


Figure 4. Voltage Drop versus Load Current @ $V_{IN} = 1.5 \text{ V}$

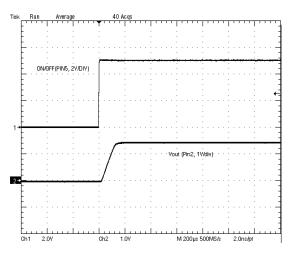
TYPICAL PERFORMANCE CURVES (T $_{J}$ = 25°C unless otherwise noted)



Yout (Pin2, 0.5Y/div)

Figure 5. Turn-on $(V_{in} = 1.5 \text{ V}, R_L = 3 \Omega, R1 = 1 \text{ k}\Omega, R2 = 0, C1 = 47 \text{ nF})$

Figure 6. Turn-off $(V_{in} = 1.5 \text{ V}, R_L = 3 \Omega, R1 = 1 \text{ k}\Omega, R2 = 0, C1 = 47 \text{ nF})$



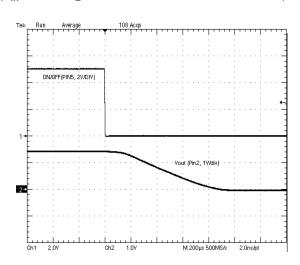
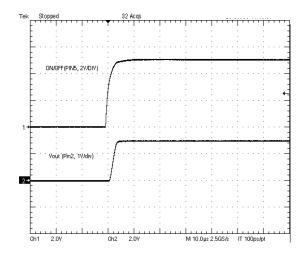


Figure 7. Turn-on

Figure 8. Turn-off $(V_{in} = 1.5 \text{ V}, R_L = 3 \Omega, R1 = 10 \text{ k}\Omega, R2 = 1 \text{ k}\Omega, C1 = 47 \text{ nF})$ $(V_{in} = 1.5 \text{ V}, R_L = 3 \Omega, R1 = 10 \text{ k}\Omega, R2 = 1 \text{ k}\Omega, C1 = 47 \text{ nF})$



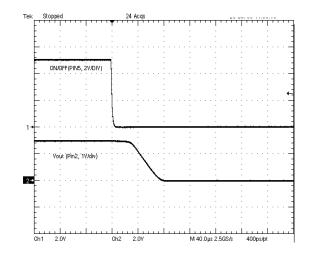


Figure 9. Turn-on $(V_{in} = 3 \ V, \ R_L = 3 \ \Omega, \ R1 = 10 \ k\Omega, \ R2 = 1 \ k\Omega, \ C1 = 47 \ nF) \\ (V_{in} = 3 \ V, \ R_L = 3 \ \Omega, \ R1 = 10 \ k\Omega, \ R2 = 1 \ k\Omega, \ C1 = 47 \ nF)$

Figure 10. Turn-off

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

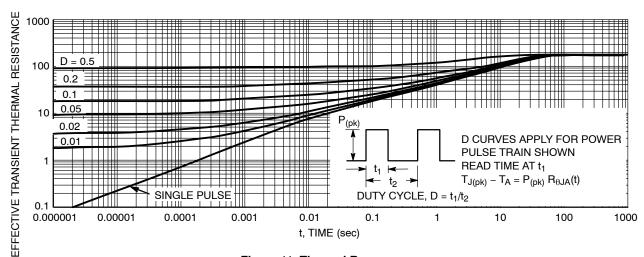


Figure 11. Thermal Response

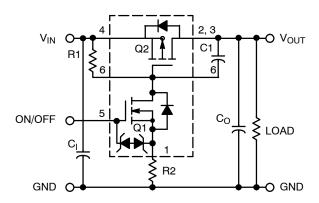


Figure 12. Load Switch Application

Components	Description	Value	
R1	R1 Pull-up Resistor Typical 10 kΩ to 1.0 MΩ*		
R2	Optional Slew-Rate Control	Typical 0 k Ω to 100 k Ω *	
C _O , C _I	Output Capacitance	Usually < 1.0 μF	
C1	Optional In-Rush Current Control	Typical ≤ 1000 pF	

^{*}Minimum R1 value should be at least 10 x R2 to ensure Q1 turn-on.

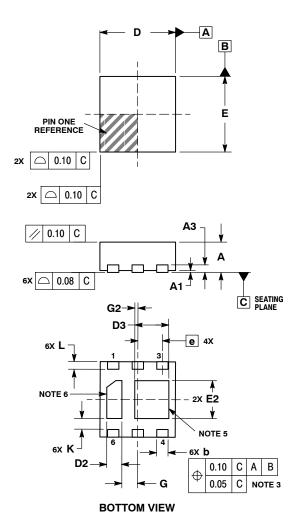
ORDERING INFORMATION

Device	Package	Shipping [†]
NTLJD2105LTBG	WDFN6 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

WDFN6, 2x2 CASE 506AZ ISSUE A

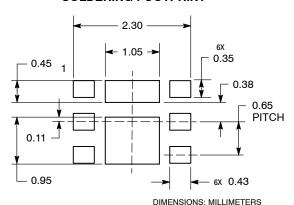


NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994
- CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20mm FROM TERMINAL
- COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
 PINS 2 & 3 CONNECTED TO LARGE FLAG.
- PIN 6 CONNECTED TO SMALL FLAG.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.70	0.80	
A1	0.00	0.05	
A3	0.20	REF	
b	0.25 0.35		
D	2.00 BSC		
D2	0.30	0.50	
D3	0.80	1.00	
E	2.00 BSC		
E2	0.90 1.10		
е	0.65 BSC		
G	0.41 REF		
G2	0.085 REF		
K	0.25 REF		
L	0.20	0.30	

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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